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### November 2013

# FQPF27N25

# N-Channel QFET<sup>®</sup> MOSFET 250 V, 14 A, 110 m $\Omega$

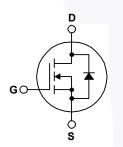
# Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

### Features

- 14 A, 250 V,  $R_{DS(on)}$  = 110 m $\Omega$  (Max.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 7 A
- Low Gate Charge (Typ. 50 nC)
- Low Crss (Typ. 45 pF)
- 100% Avalanche Tested





## Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

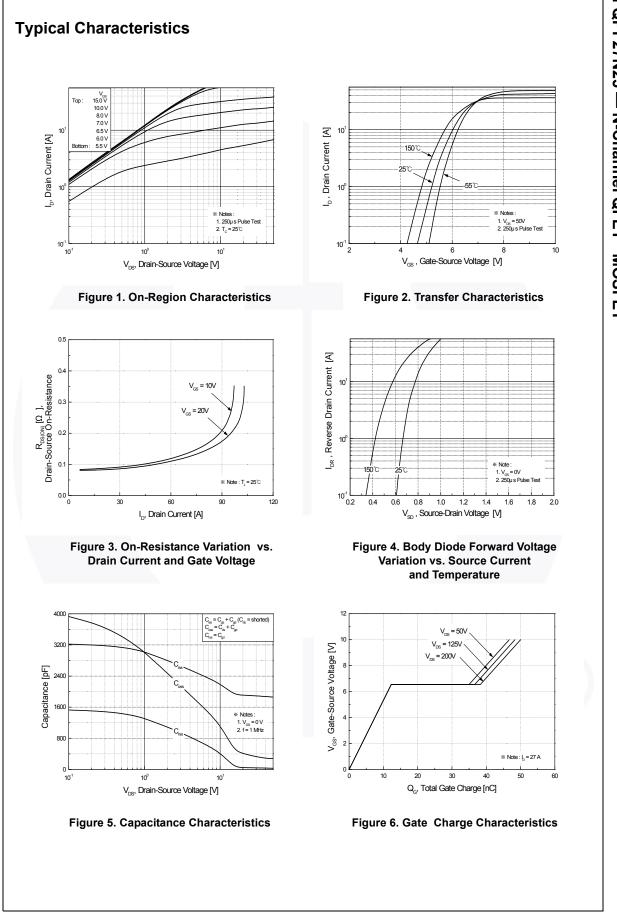
Symbol	Parameter		FQPF27N25	Unit
V <sub>DSS</sub>	Drain-Source Voltage		250	V
I <sub>D</sub>	Drain Current - Continuous ( $T_C = 25^\circ$	C)	14	A
	- Continuous (T <sub>C</sub> = 100	°C)	8.9	A
DM	Drain Current - Pulsed	(Note 1)	56	А
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	600	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	14	A
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	(Note 1) 5.5	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5	V/ns
PD	Power Dissipation ( $T_C = 25^{\circ}C$ )		55	W
	- Derate above 25°C		0.44	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Ran	ge	-55 to +150	°C
TL	Maximum Lead Temperature for Solderin 1/8" from Case for 5 seconds	g,	300	°C

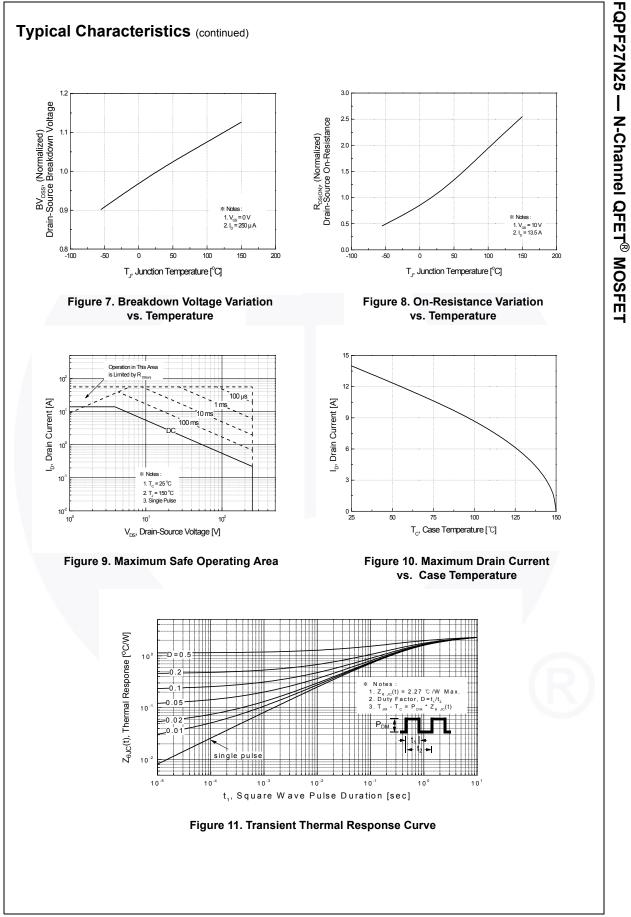
# **Thermal Characteristics**

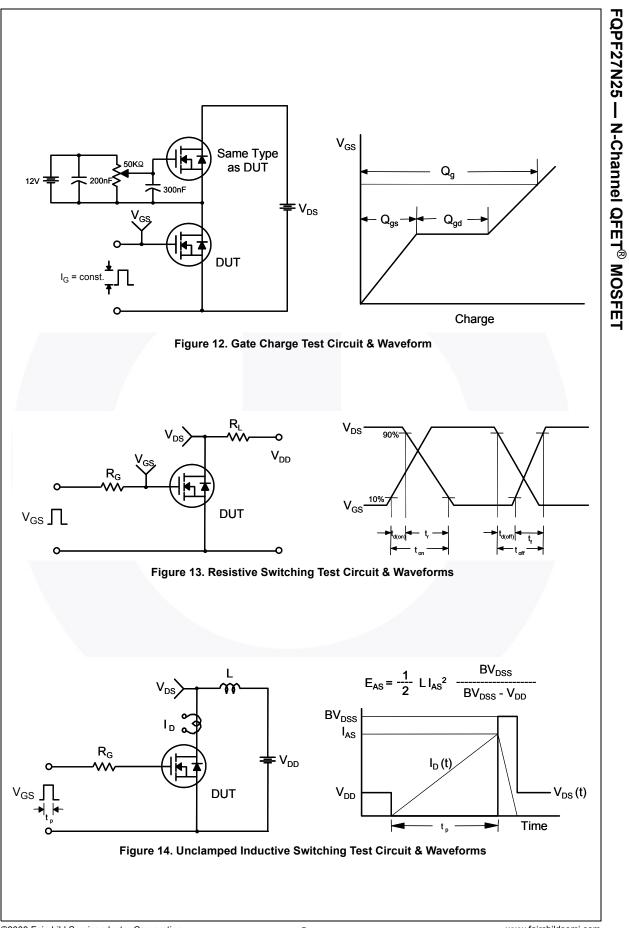
Symbol	Parameter	FQPF27N25	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	2.27	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

Part Nu	art Number Top Mark Package		Packing Method	Reel Size	Tape Width		h Q	Quantity	
FQPF27N25 FQPF27N25 TO-220F		Tube N/A		N/A		5	50 units		
lectri	cal C	haracteristics	T <sub>C</sub> = 25°C	unless otherwise noted.					
Symbol		Parameter		Test Condi	tions	Min	Тур	Max	Unit
Off Cha	raata	riation							
BV <sub>DSS</sub>		Source Breakdown V	oltaga	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA		250			V
BV <sub>DSS</sub>				V <sub>GS</sub> = 0 V, 1 <sub>D</sub> = 230 μA		230			v
$\Delta T_{J}$	Breakdown Voltage Temperature Coefficient		alure	$I_D = 250 \ \mu$ A, Referenced to $25^{\circ}$ C			0.29		V/°C
DSS				V <sub>DS</sub> = 250 V, V <sub>GS</sub> =	0 V			1	μA
	Zero C	Gate Voltage Drain Cu	urrent	$V_{\rm DS}$ = 200 V, T <sub>C</sub> = 1				10	μΑ
GSSF	Gate-I	Body Leakage Currer	nt, Forward	$V_{GS}$ = 30 V, $V_{DS}$ = 0	V			100	nA
GSSR	Gate-I	Body Leakage Currer	nt, Reverse	$V_{GS}$ = -30 V, $V_{DS}$ =	0 V			-100	nA
On Cha	aracte	ristics							
/ <sub>GS(th)</sub>	1	Threshold Voltage		$V_{DS} = V_{GS}, I_D = 250$	) μA	3.0		5.0	V
R <sub>DS(on)</sub>		Drain-Source		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7.0		-	0.083	0.11	Ω
FS	Forwa	rd Transconductance	•	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 7.0	A		15		S
Dvnam	ic Cha	racteristics							
viss	1	Capacitance		V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0	) V		1900	2450	pF
Poss	Outpu	t Capacitance		f = 1.0 MHz	, <b>v</b> ,		360	470	pF
rss	Rever	se Transfer Capacita	nce				45	60	pF
Switch		aracteristics							
d(on)		On Delay Time		V <sub>DD</sub> = 125 V, I <sub>D</sub> = 2	7 A,		32	75	ns
r	Turn-0	On Rise Time		$R_G = 25 \Omega$			270	550	ns
d(off)	Turn-0	Off Delay Time					80	170	ns
	Turn-0	Off Fall Time			(Note 4)		120	250	ns
ζ <sub>g</sub>	Total C	Gate Charge		V <sub>DS</sub> = 200 V, I <sub>D</sub> = 27	7 A,		50	65	nC
2 <sub>gs</sub>	Gate-	Source Charge		V <sub>GS</sub> = 10 V			12.5		nC
λ <sub>gd</sub>	Gate-I	Drain Charge			(Note 4)	-	26	-	nC
Drain-S	Source	Diode Characte	eristics an	d Maximum Rat	inas				
S	1	um Continuous Drair						14	Α
SM	Maximum Pulsed Drain-Source Diode Forward Current					56	Α		
/ <sub>SD</sub>	Drain-	Source Diode Forwar	d Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 14 A	1			1.5	V
rr		se Recovery Time		$V_{GS} = 0 V, I_S = 27 A$			220		ns
יי גיי		se Recovery Charge		dl <sub>F</sub> / dt = 100 A/μs			1.8		μC
	1	, 3-					-		

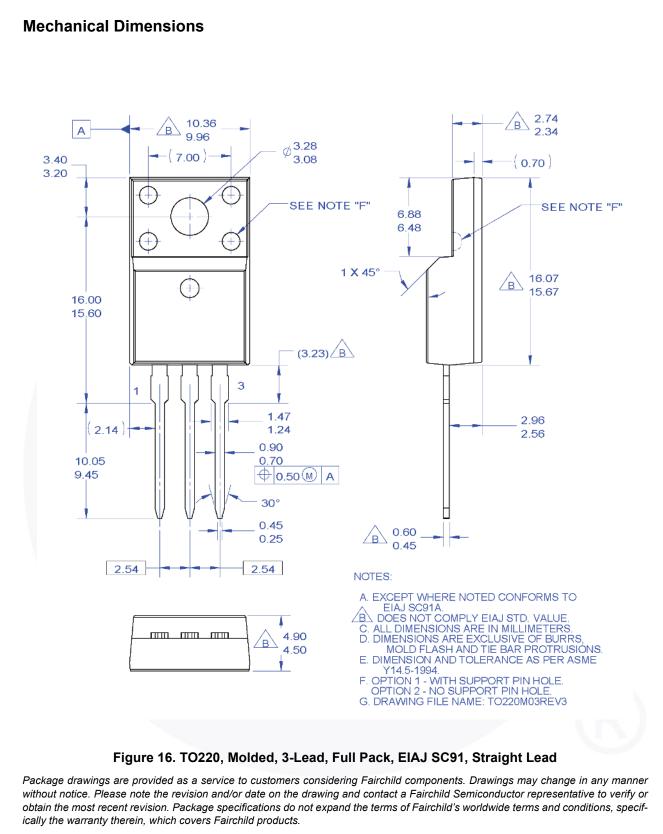
FQPF27N25 — N-Channel QFET<sup>®</sup> MOSFET







DUT +  $v_{DS}$ ۱<sub>sd</sub> م L Driver R<sub>G</sub>, Same Type as DUT L F V<sub>DD</sub>  $\prod V_{GS}$ • dv/dt controlled by  $R_{G}$ • I<sub>SD</sub> controlled by pulse period Î Gate Pulse Width  $V_{GS}$ D = Gate Pulse Period 10V (Driver)  $\mathbf{I}_{\text{FM}}$  , Body Diode Forward Current I <sub>SD</sub> di/dt (DUT)  $I_{RM}$ Body Diode Reverse Current  $V_{DS}$ (DUT) Body Diode Recovery dv/dt  $V_{SD}$ V<sub>DD</sub> Body Diode Forward Voltage Drop Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

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FQPF27N25 — N-Channel QFET<sup>®</sup> MOSFET



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